

## N-Channel Enhancement Mode Power MOSFET

### **Description**

The MS50N60 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-220F package is universally preferred for all commercial-industrial applications

#### **Features**

- · Low On Resistance
- Simple Drive Requirement
- · Low Gate Charge
- · Fast Switching Characteristic
- RoHS compliant package

### **Application**

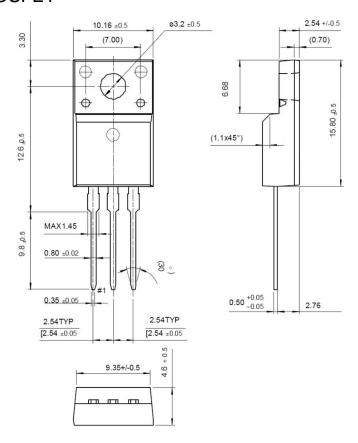
- Power Factor Correction
- · LCD TV Power
- · Full and Half Bridge Power
- · E-bike Charger

#### **Packing & Order Information**

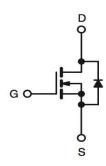
50/Tube; 1,000/Box







### **Graphic symbol**



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)				
Symbol	Parameter	Value	Unit	
$V_{DS}$	Drain-Source Voltage	60	V	
$V_{GS}$	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Continuous Drain Current @ TC=25°C	50	А	
	Continuous Drain Current @ TC=100°C	35	Α	
I <sub>DM</sub> *1	Pulsed Drain Current	200	А	
I <sub>AS</sub>	Avalanche Current	50	А	
E <sub>AS</sub>	Avalanche Energy	500	mJ	



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Absolute Maximum Ratings (Tc=25°C unless otherwise specified)				
Symbol	ymbol Parameter Value U		Unit	
E <sub>AR</sub> *2	Repetitive Avalanche Energy	12	mJ	
dv/dt	Peak Diode Recovery dv/dt	4.5	V/ns	
D	Power Dissipation (TC=25°C)	120	W	
$P_{D}$	Power Dissipation (TC=100°C)	0.8	W	
T <sub>J</sub> /T <sub>STG</sub>	Operating Junction and Storage Temperature	-55 to +175	°C	

### NOTE:

- 1. Pulse width limited by maximum junction temperature.
- 2. L=200 $\mu$ H, I<sub>AS</sub>=50A,V<sub>DD</sub>=30V, starting TJ=+25°
- 3.  $I_{SD} \le 50A$ ,  $dI/dt < 100A/\mu s$ ,  $VDD \le BVDSS$ ,  $TJ \le Tj(max)$ .

Thermal Resistance Ratings(Tc=25°C unless otherwise noted)				
Parameter	Symbol	Value	Units	
Rthjc	Toward the arread vacintons	1.24	°C/W	
RθJA	Typical thermal resistance	62.5	C/VV	

Static Characteristics					
Symbol	Test Conditions	Min	Тур.	Max.	Units
BDVSS	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu A$	60			V
$V_{GS}$	$V_{DS} = V_{GS}$ , $I_{D} = -250 \mu A$	2.0	2.8	4.0	V
<b>g</b> fs	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		28		S
I <sub>GSS</sub>	$V_{GS} = \pm 20$			±100	nA
I <sub>DSS</sub>	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			5 25	uA
I <sub>D(on)</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α
*R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_{D} = 30 \text{ A}$ $V_{GS} = 15 \text{ mV}, V_{SD} = 0 \text{ , } f = 1 \text{MHz}$		19 28	22	mΩ

Dynamic Characteristics					
Symbol	Test Conditions	Min	Тур.	Max.	Units
$t_{\text{d(on)}}$					ns
t <sub>r</sub>	$V_{DS} = 50 \text{ V}$ , $R_D = 6 \Omega$ ,				ns
$t_{d(off)}$	V <sub>GS</sub> = 10 V , I <sub>D</sub> = 1 A				ns
t <sub>f</sub>					ns
C <sub>ISS</sub>					pF
Coss	$V_{DS} = 25 \text{ V}$ , $V_{GS} = 0 \text{ V}$ f = 1 MHz				pF
C <sub>RSS</sub>					pF



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Dynamic Cha	Dynamic Characteristics				
Symbol	Test Conditions	Min	Тур.	Max.	Units
Rg					Ω
$\overline{Q_g}$	$V_{DS} = 80 \text{ V}, I_{D} = 30 \text{ A},$				nC
$Q_gs$	V <sub>GS</sub> = 10 V				nC
$Q_gd$					nC

### NOTE:

- 1. Pulse Test : Pulse Width ≤300µs, Duty Cycle≤2%
- 2. Independent of operating temperature
- 3. Pulse width limited by maximum junction temperature.

Source-Drain Diode Characteristics					
Symbol	Test Conditions	Min	Тур.	Max.	Units
Is				50	A
I <sub>SM</sub>				140	
V <sub>SD</sub>	IS = 25 A , V <sub>GS</sub> = 0			1.3	V
t <sub>rr</sub>	IF 50 A M 0 HF/H 400A/		22		ns
Q <sub>rr</sub>	$IF = 50 \text{ A}$ , $V_{GS} = 0$ , $dIF/dt = 100A/\mu s$		180		uC

Ordering Information	
Parameter	Shipping
TO-220	50 pcs/tube, 20 tubes/box, 4 boxes / carton



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